

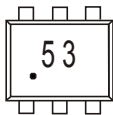
Plastic-Encapsulate Diodes

SWITCHING DIODE

FEATURES

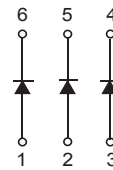
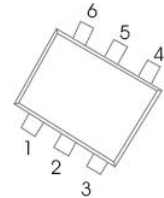
- Fast Switching Speed
- For General Purpose Switching Applications
- High Conductance

Marking: 53



Solid point=Pin1 positioning point

SOT-563



Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25°C

Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	100	V
Peak Repetitive Peak Reverse Voltage	V_{RRM}	75	V
Working Peak Reverse Voltage	V_{RWM}		
DC Blocking Voltage	V_R		
RMS Reverse Voltage	$V_{R(RMS)}$	53	V
Forward Continuous Current	I_{FM}	300	mA
Average Rectified Output Current	I_O	200	mA
Non-Repetitive Peak Forward Surge Current @t=8.3ms	I_{FSM}	2.0	A
Power Dissipation	P_d	150	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	833	°C/W
Operation Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	°C

Electrical Ratings @Ta=25°C

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Reverse breakdown voltage	$V_{(BR)}$	75			V	$I_R=100 \mu A$
Forward voltage	V_{F1}			0.715	V	$I_F=1mA$
	V_{F2}			0.855	V	$I_F=10mA$
	V_{F3}			1.0	V	$I_F=50mA$
	V_{F4}			1.25	V	$I_F=150mA$
Reverse current	I_{R1}			1	μA	$V_R=75V$
	I_{R2}			25	nA	$V_R=20V$
Capacitance between terminals	C_T			2	pF	$V_R=0V, f=1MHz$
Reverse recovery time	t_{rr}			4	ns	$I_F=I_R=10mA$ $I_{rr}=0.1 \times I_R, R_L=100\Omega$



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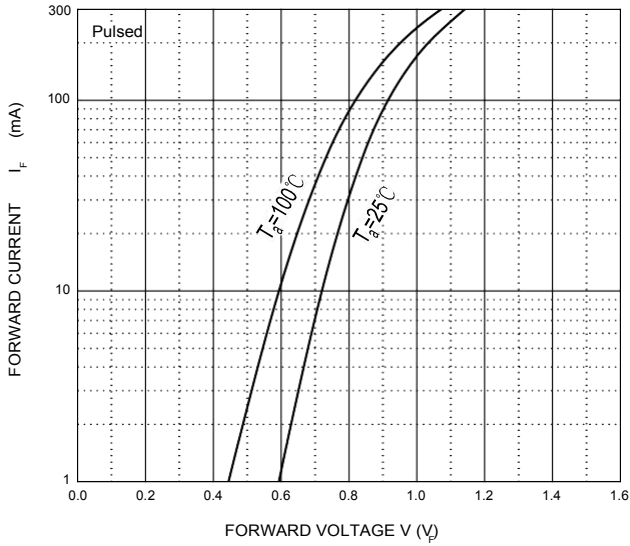
BAS16VV



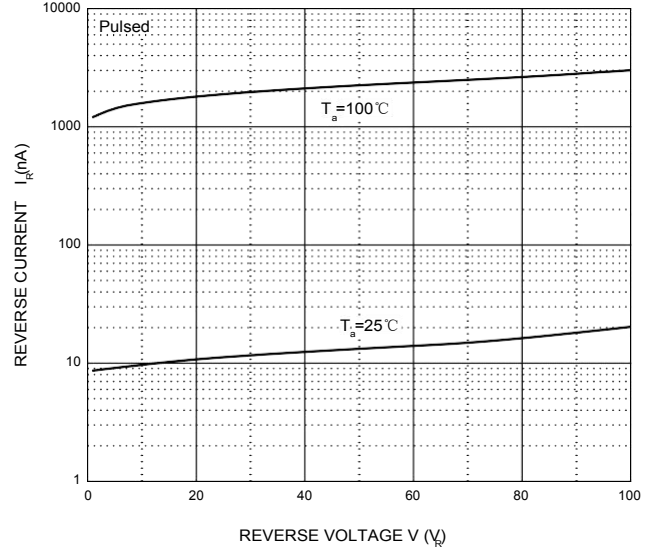
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Typical Characteristics

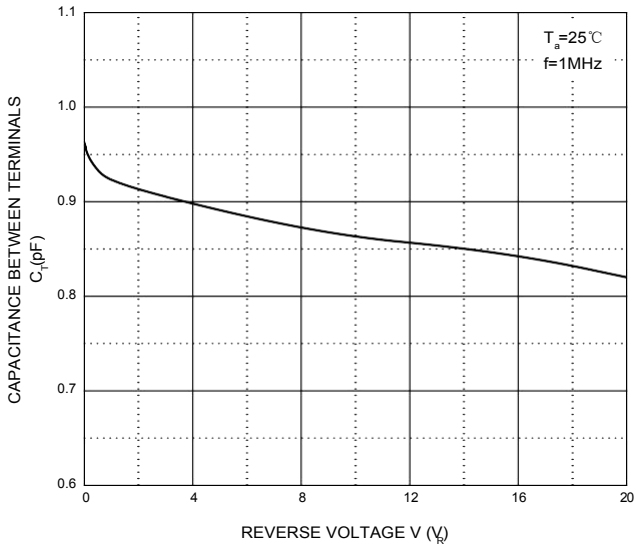
Forward Characteristics



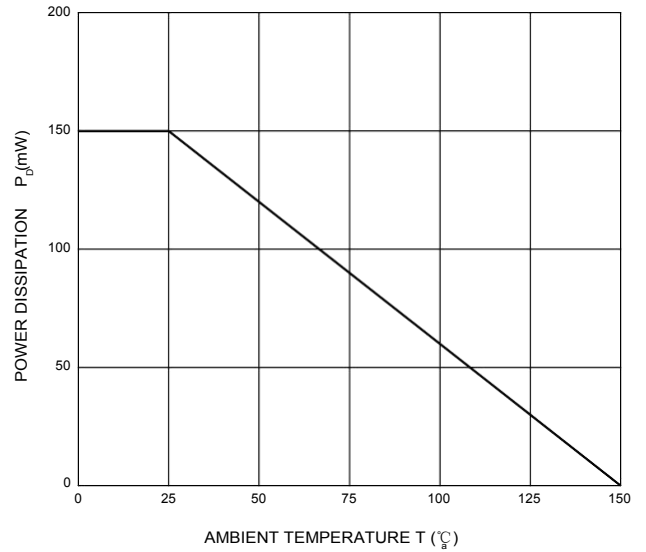
Reverse Characteristics



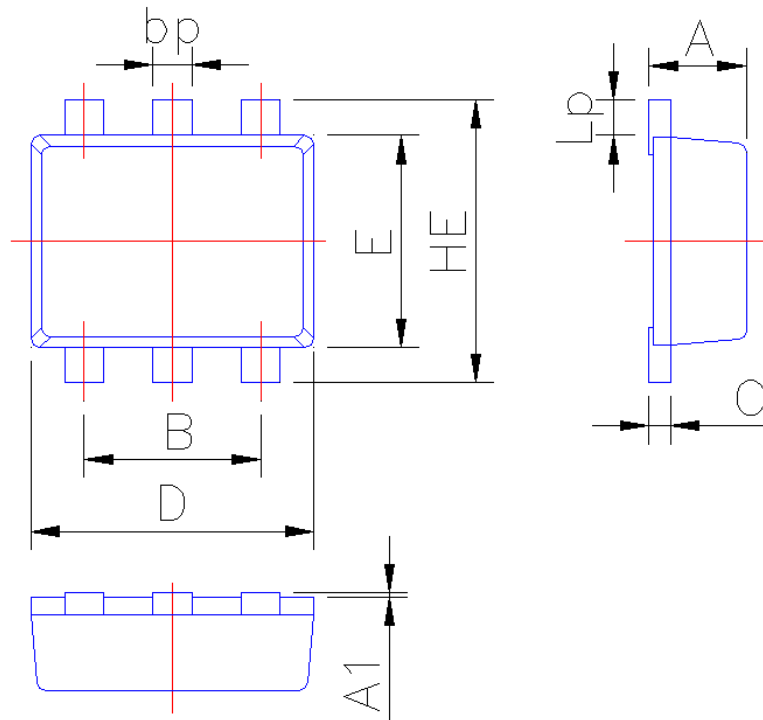
Capacitance Characteristics



Power Derating Curve



SOT-563 Package Outline Dimensions



Symbol	Dimension in Millimeters	
	Min	Max
A	0.50	0.60
A1	0	0.05
B	0.95	1.05
bp	0.13	0.30
C	0.09	0.150
D	1.50	1.70
E	1.15	1.35
HE	1.40	1.80
Lp	0.13	0.30